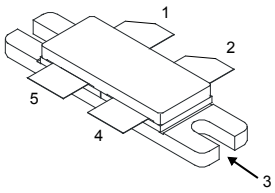
ST05250

Datasheet

250 W, 28/32 V, HF to 1 GHz, RF Power LDMOS transistor



B4E

Pin connection	
Pin	**Connection**
1	Drain A
2	Drain B
3	Source (bottom side)
4	Gate B
5	Gate A

STPOWER

Product status link
ST05250

Product summary	
Order code	ST05250
Marking	ST05250
Package	B4E
Packing	Tape and reel 13"
Base / Bulk qty	120 / 120

Features

Order code	Frequency	V_{DD}	P_{OUT}	Gain	Efficiency
ST05250	945 MHz	28 V	250 W	13.5 dB	52 %

- High efficiency and linear gain operations
- Integrated ESD protection
- Large positive and negative gate-source voltage range for improved class C operation
- In compliance with the european directive 2002/95/EC

Applications

- 2 – 30 MHz HF or short wave communication
- 30 – 88 MHz ground communication
- 118 – 140 MHz avionics
- 136 – 174 MHz commercial ground communication
- 30 – 512 MHz jammer, ground/air communication
- HF – 1 GHz ISM - instrumentation

Description

The ST05250 is a 250 W, 28/32 V LDMOS FETs, designed for wideband communication and ISM applications in the frequency range from HF to 1 GHz. It can be used in class AB, B or C for all typical modulation formats.

1 Electrical ratings

Table 1. Absolute maximum ratings (T_{CASE}= 25 °C)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	90	V
V_{GS}	Gate-source voltage	-8 to 10	V
V_{DD}	Maximum operating voltage	36	V
T_{STG}	Storage temperature range	-65 to 150	°C
T_J	Maximum junction temperature	200	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC} (1)	Thermal resistance, junction-to-case	0.32	°C/W

1. *T_C= 85 °C, T_J=200 °C, DC test.*

Table 3. ESD protection

Symbol	Parameter	Class
HBM	Human body model (according to ANSI/ESDA/JEDEC JS001-2017)	2
CDM	Charge device model (according to ANSI/ESDA/JEDEC JS-002-2014)	C3

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified).

Table 4. Static (per side)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	90			V
I_{DSS}	Zero-gate voltage drain current	V_{GS} = 0 V, V_{DS} = 28 V			1	nA
		V_{GS} = 0 V, V_{DS} = 75 V				
I_{GSS}	Gate-body leakage current	V_{GS} = -8/+10 V, V_{DS} = 0 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = 28 V, I_D = 650 µA	1		3	V
$V_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 0.7 A			0.21	V
C_{iss}	Common source input capacitance	V_{GS}= 0 V, V_{DD} = 28 V, f = 1 MHz		123		pF
C_{oss}	Common source output capacitance			2.5		
C_{rss}	Common source feedback capacitance			40		

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
P_{OUT}	Output power	f = 945 MHz, 3dB compression	-	250		W
G_{PS}	Power gain		-	13.5		dB
η_D	Drain efficiency		-	52		%
VSWR	Load mismatch	At P_{OUT} = 250 W all phases	-		10:1	

Note: V_{DD} = 28 V, I_{DQ} = 500 mA, pulsed CW, pulse width = 20 µs, duty cycle = 10%.

3 Typical performances

Figure 1. P_{1dB} and drain efficiency versus frequency (2 - 130MHz)

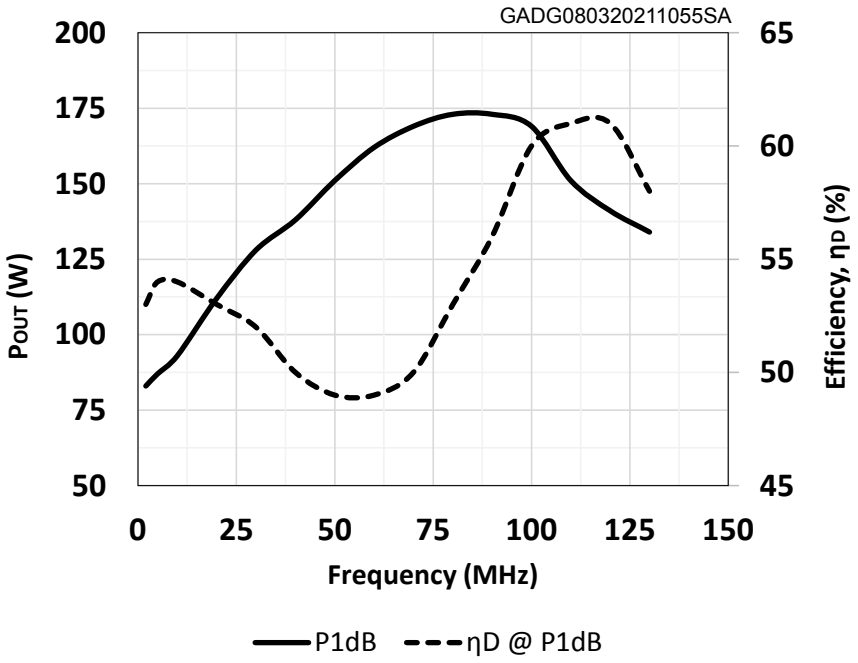


Figure 2. P_{3dB} and drain efficiency versus frequency (2 - 130 MHz)

Figure 3. P_{3dB} and drain efficiency versus frequency (30 - 512 MHz)

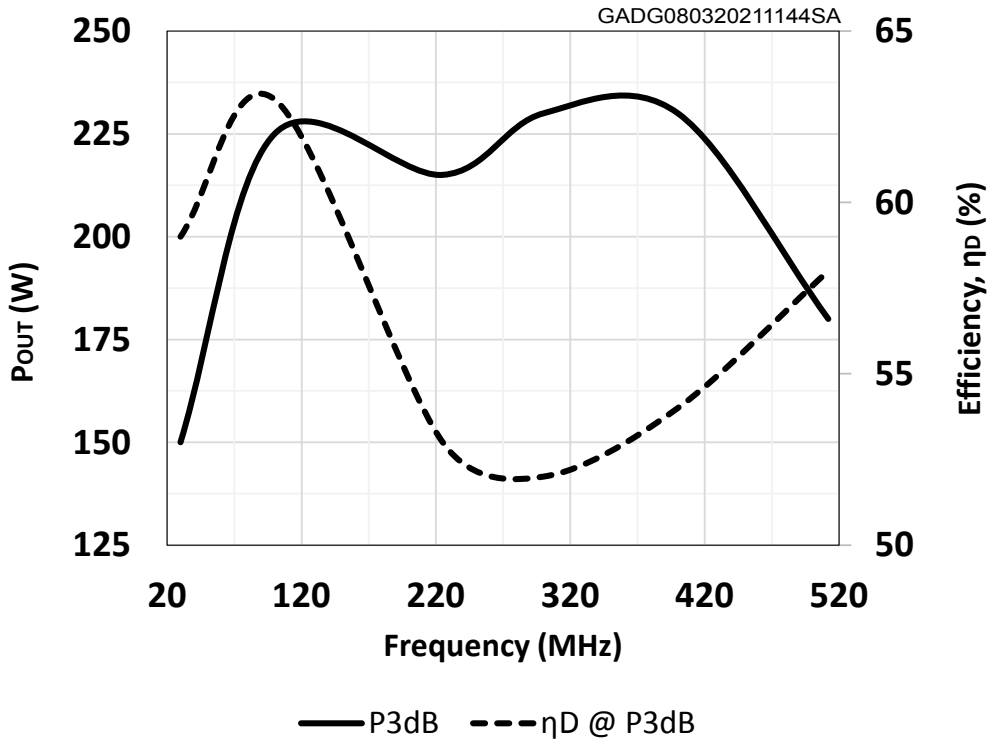
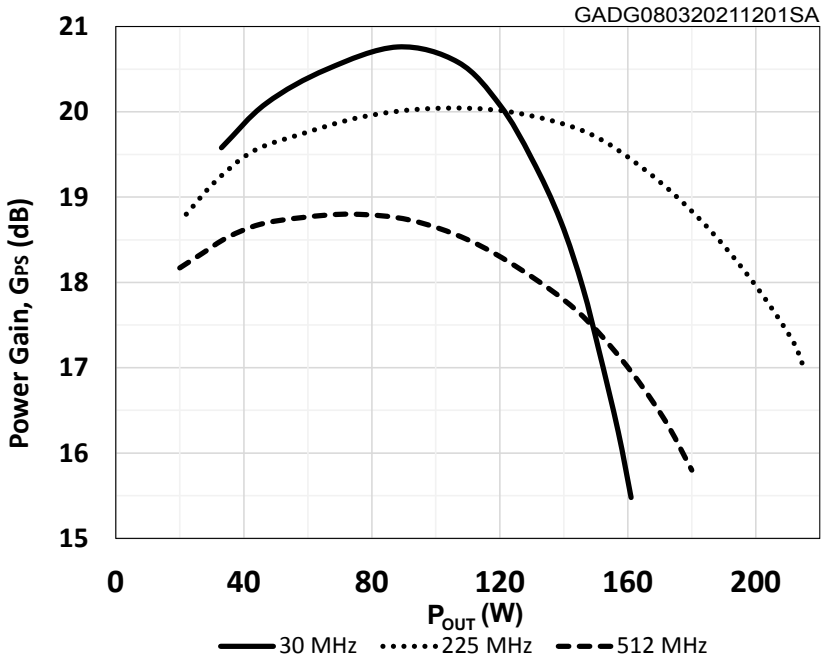


Figure 4. Power gain versus output power (30 - 512 MHz)



Note: V_{DD} = 28 V, I_{DQ} = 200 mA, CW signal.

Figure 5. **Power gain and drain efficiency versus output power (f=945 MHz)**

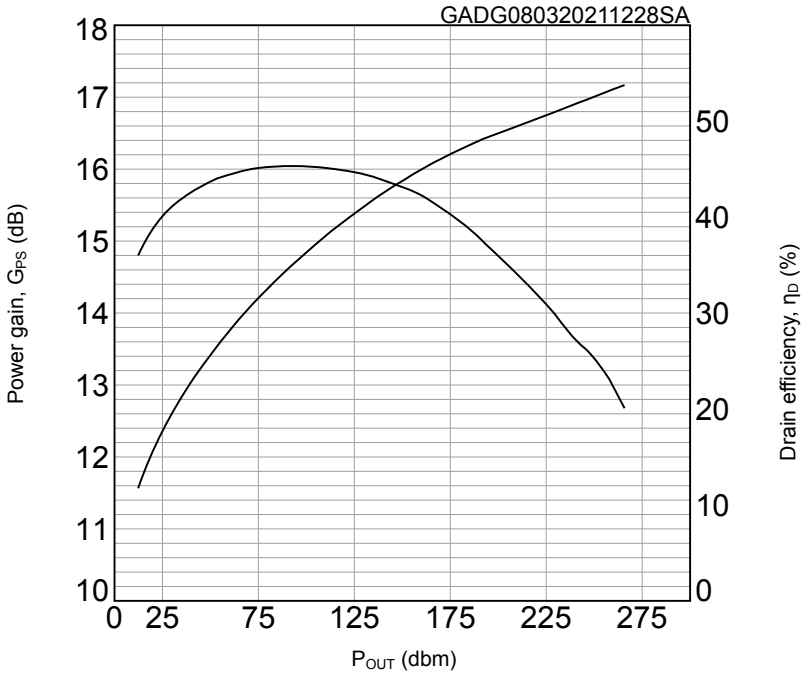
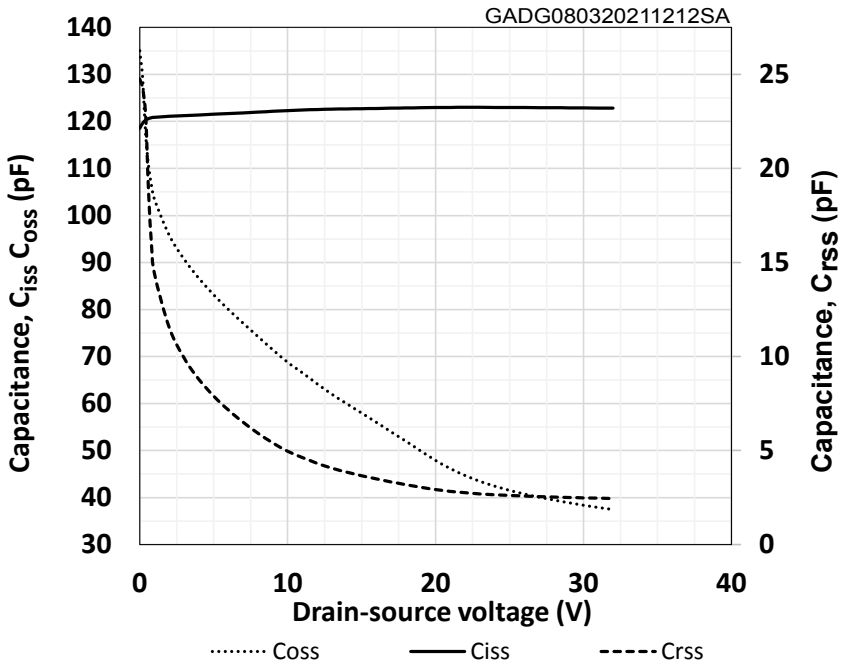


Figure 6. **Capacitance vs drain voltage at 1 MHz**



4 Impedance

Figure 7. Current conventions

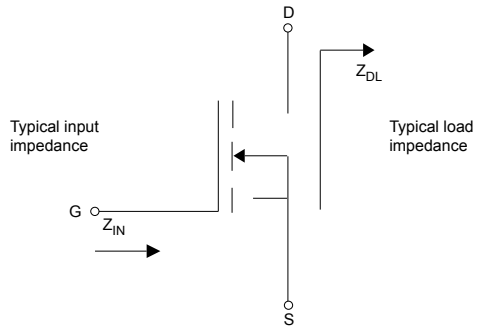


Table 6. Impedance data

Frequency	$Z_{in}(\Omega)$	$Z_{DL}(\Omega)$
2	49.9 -j2.26	5 +j0.002
5	49.35 -j5.6	5+j0.005
10	47.5 -j10.75	5+j0.01
20	41.3 - j18.6	5+j0.02
30	34 -j22.8	5+j0.03
50	22 -j24	4.99+j0.047
70	14.6 -j21.6	4.99+j0.066
90	10.35 -j18.8	4.982+j0.084
100	8.5 -j17.5	4.98+j0.1
200	3.37 -j10.8	4.91+j0.17
300	1.6 -j6.7	4.8+j0.24
400	1.59 -j4.3	4.76+j0.245
500	1.64 -j4.35	4.53 +j0.225
600	1.19-j2.22	4.34+j0.29
700	1.175-j1.55	4.15+j0.24
800	1.16-j0.98	3.96+j0.155
900	1.16-j0.49	3.76+j0.04
1000	1.155-j0.05	3.58-j0.1

Note: Measured gate-to-gate and drain-to-drain, respectively (balanced configuration).

5 Test circuits

Figure 8. **Test circuit photo (2 - 130 MHz)**

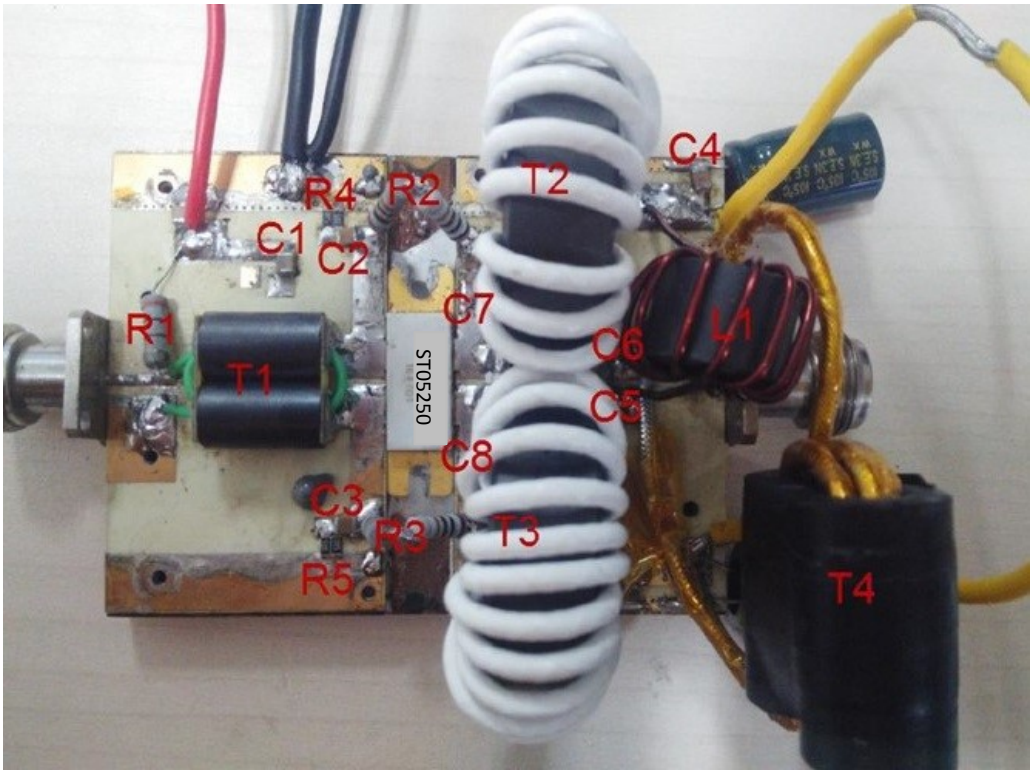


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Table 7. **Components list (2 - 130 MHz)**

Component	Value	Description/manufacturer
C1, C2, C3, C4, C5, C6, C7, C8	10 µF	100 V ceramic multilayer capacitor
R1, R2, R3	300 Ω	3 W chip resistor
R4, R5	27 Ω	3 W chip resistor
T1	4:1 transformer	Fair rite 2843000202
T2, T3	TC-22 13 turns	AMI DONCORP FT-140-73 UI = 2500
T4	50 Ω - 4 turns	Fair rite 2643625102 UI = 800
L1	12 turns	Fair rite 2643665802 UI = 800
PCB	0.762 mm [0.030"] thick, ε_r = 3.48, Rogers RO4350B	

Figure 9. **Test circuit photo (30 - 512 MHz)**

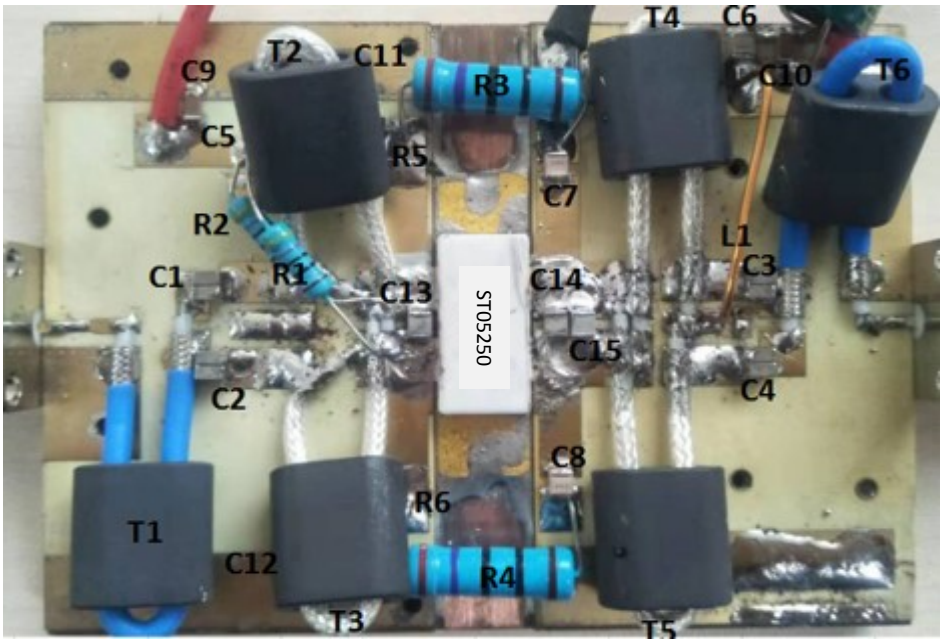

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Figure 10. **Test circuit schematic (30 - 512 MHz)**

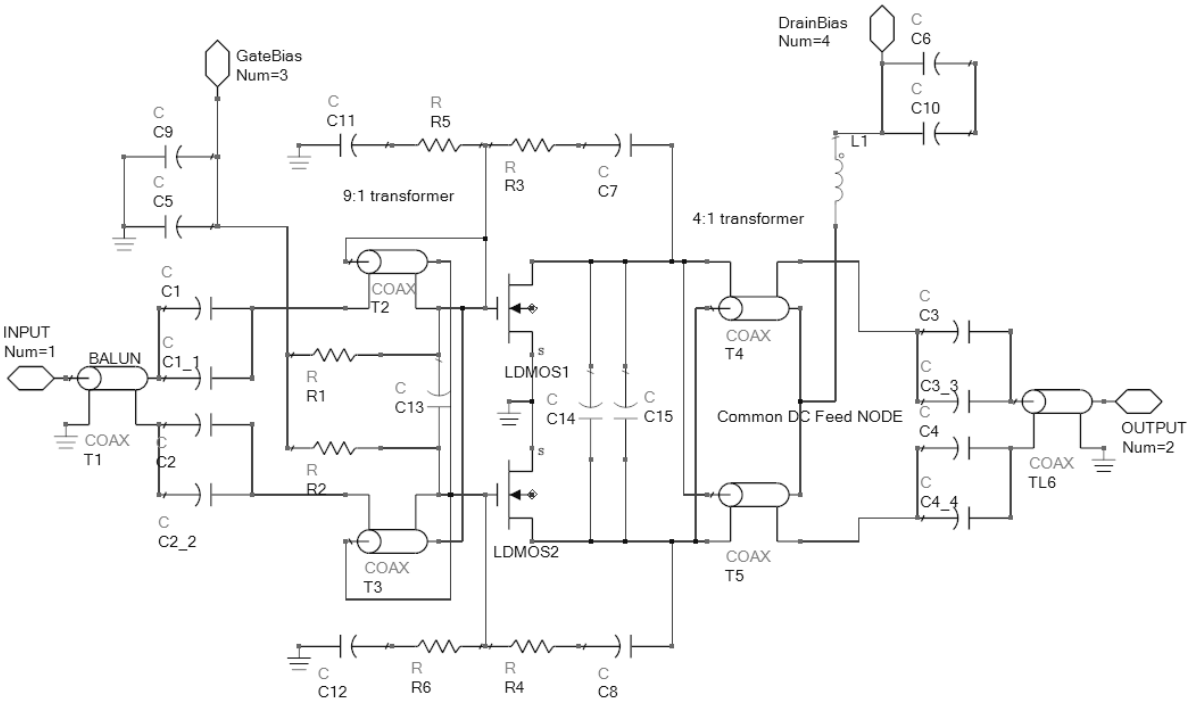

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Table 8. Components list (30 - 512 MHz)

Component	Value	Description/manufacturer
C1, C2, C3, C4	120 pF	ATC800B
C5, C6, C7, C8	1 nF	DCL70B
C9, C10, C11, C12	10 µF	100V ceramic multilayer capacitor
C13, C14, C15	10 pF	ATC800B
R1, R2	470 Ω	1 W
R3, R4	270 Ω	3 W
R5, R6	2*33 Ω	0805 chip resistor
T1, T6	50 Ω - 70 mm	BN-61-202 SF-086-1.5
T2, T3	17.5 Ω - 70 mm	BN-61-202 SFF-17.5-1.5
T4, T5	12.5 Ω - 70 mm	BN-61-202 SFF-12.5-1.5
L1	40 mm	Diameter = 0.7 mm
PCB	0.762 mm (0.030") thick, ε_r = 3.48, Rogers RO4350B	

Figure 11. Test circuit photo (f= 945 MHz)

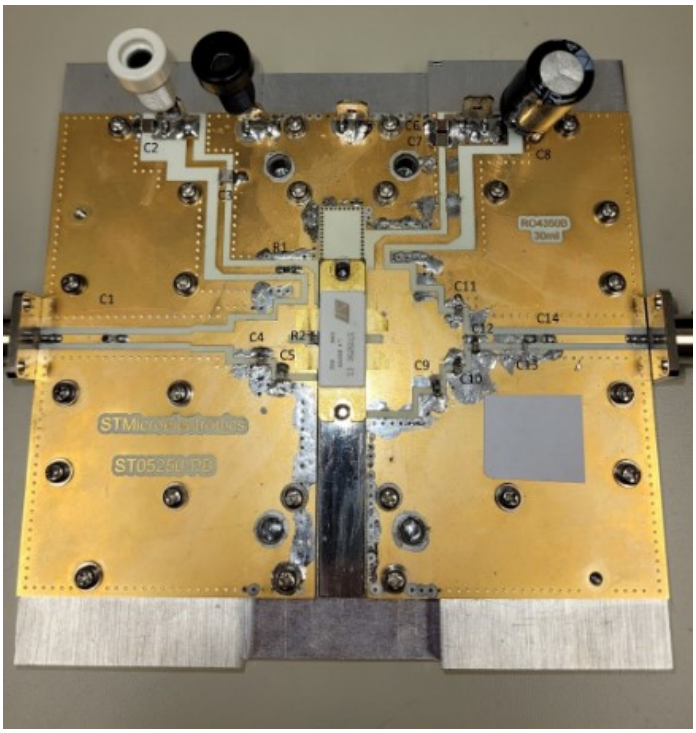

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Table 9. **Components list (f= 945 MHz)**

Component	Value	Description/manufacturer
C1, C14	39 pF	ATC 100A
C2, C6	10 µF	1206 50 V chip capactor
C3, C7	39 pF	ATC 100B
C4	12 pF	ATC 100A
C5, C9, C10	6.8 pF	ATC 100A
C8	470 µF	63 V electrolytic
C11, C12	1.2 pF	ATC 100A
C13	0.6 pF	ATC 100A
R1, R2	10 Ω	063 chip resistor
PCB	0.762 mm (0.030") thick, ε_r = 3.48, Rogers RO4350B	

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

6.1 B4E package information

Figure 12. B4E package outline

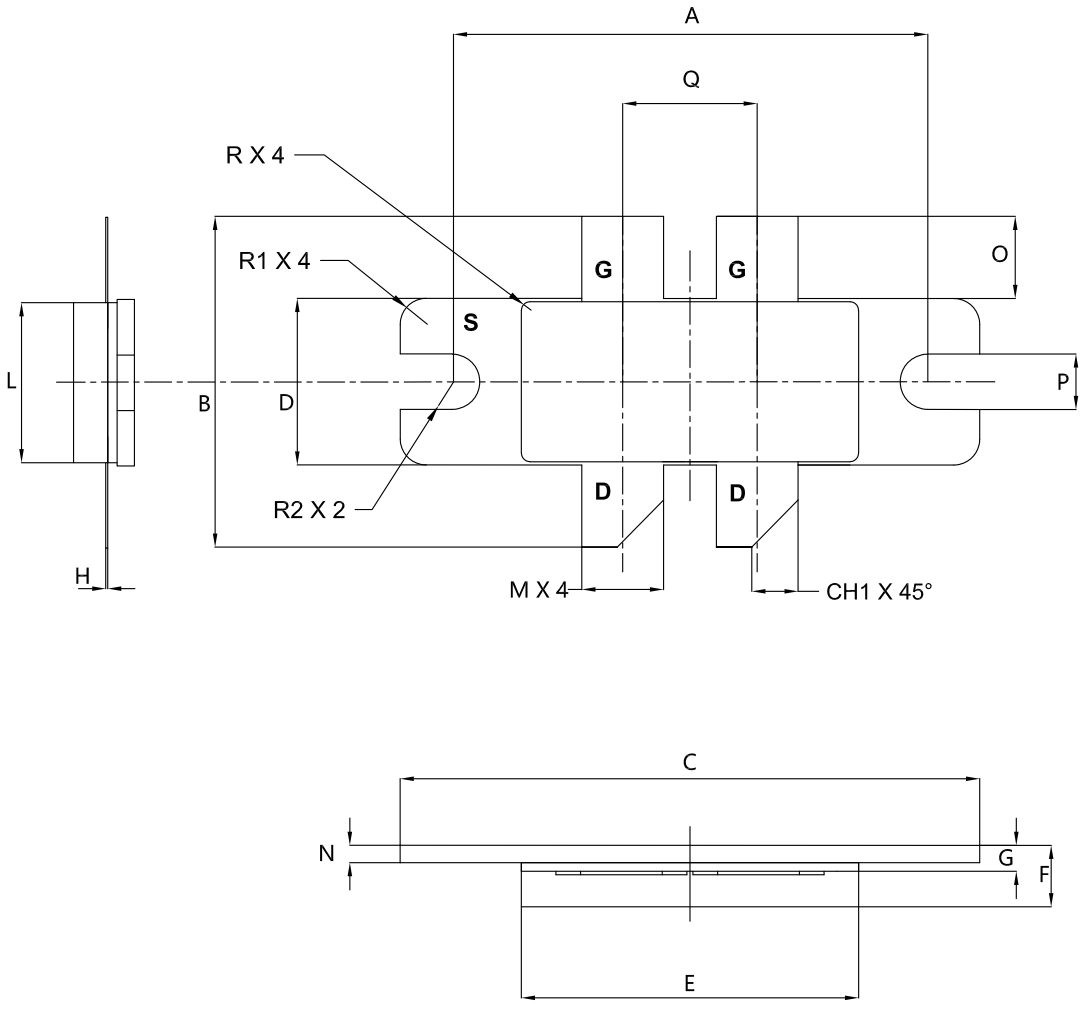

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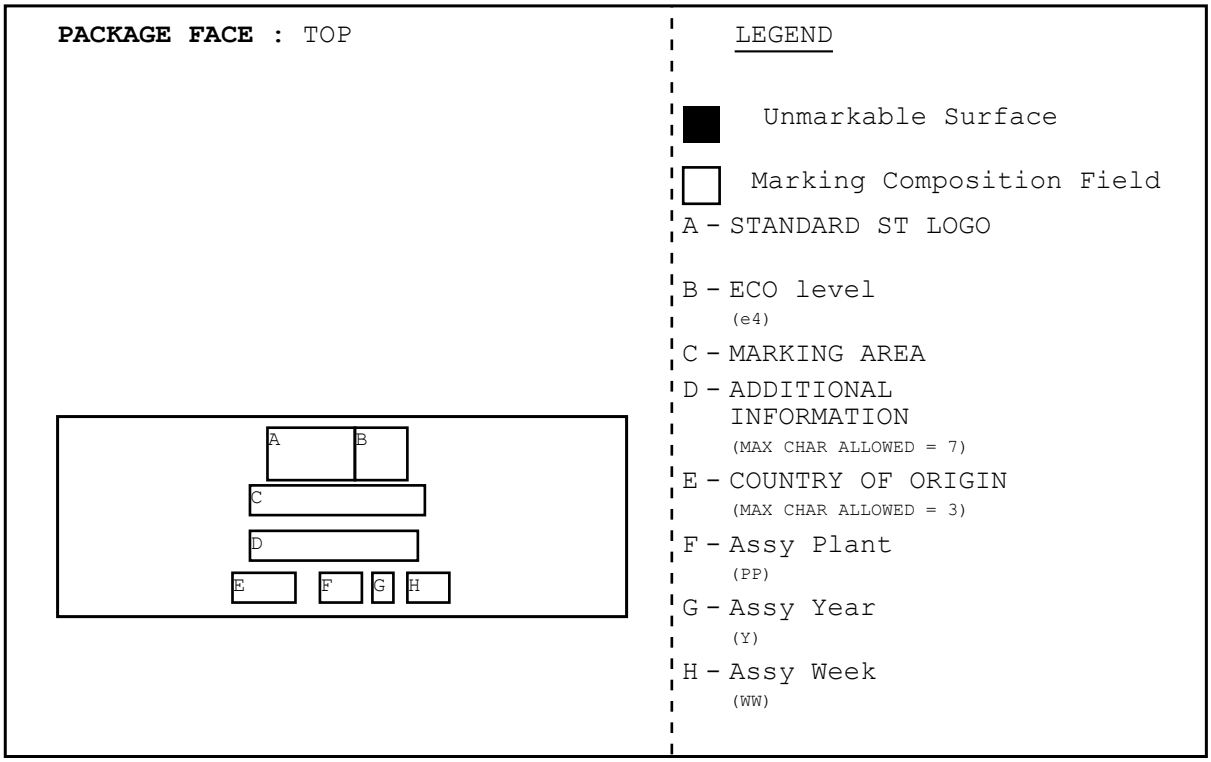
Table 10. **B4E package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	27.81	27.94	28.07
B	18.93	19.43	19.93
C	33.91	34.04	34.17
D	9.65	9.78	9.91
E	19.56	19.81	20.06
F	3.23	3.61	3.99
G	1.40	1.53	1.66
H	0.07		0.15
L	9.20	9.40	9.60
M	4.67	4.80	4.93
N	0.89	1.02	1.15
O	4.70	4.83	4.96
P	3.13	3.26	3.39
Q	7.77	7.90	8.03
R		0.50	
R1		1.52	
R2		1.63	
CH1		2.72	

7 Marking information

Figure 13. **Marking composition**



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Revision history

Table 11. **Document revision history**

Date	Version	Changes
01-Aug-2018	1	Initial release.
09-Sep-2020	2	Updated *Section Product status / summary*, *Table 5. Dynamic* and *Section 4.1 B4E package information*.
23-Nov-2020	3	Updated *Figure 1. Output power and efficiency vs frequency.* Minor text changes.
15-Mar-2021	4	Modified Gain value in features table on cover page Modified Table 2. Thermal data, Table 3. ESD protection, Table 4. Static (per side), Table 5. Dynamic. Added Section 3 Typical performance. Modified the entire Section 5 Test circuits.

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